

INFORMATION DISCLOSURE CITATION PTO-1449	ATTY. DOCKET NO. NTI-007-1D	SERIAL NO. Filed Herewith
	APPLICANT Pierrat, et al.	
	FILING DATE 9/9/2003	GROUP unknown
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)		
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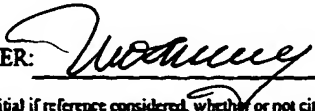
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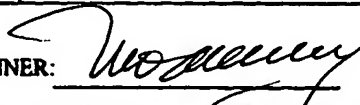
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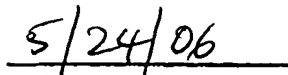
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